

KSC2258/2258A

High Voltage General Amplifier TV Video Output Amplifier

• High BV_{CEO}



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage		
	: KSC2258	250	V
	: KSC2258A	300	V
V _{CEO}	Collector-Emitter Voltage		
	: KSC2258	250	V
	: KSC2258A	300	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current (DC)	100	mA
I _{CP}	Collector Current (Pulse)	150	mA
P _C	Collector Dissipation (T _C =25°C)	4	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 0.1 \text{mA}, I_C = 0$	6			V
I _{CER}	Collector Cut-off Current	$V_{CE} = 250V, R_{BE} = 100K\Omega$			100	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = 20V, I_{C} = 40mA$	40			
h _{FE2}		$V_{CE} = 50V, I_{C} = 5mA$	30			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 50$ mA, $I_B = 5$ mA			1.2	V
V _{BE} (on)	Base-Emitter On Voltage	$V_{CE} = -20V, I_{C} = 40mA$			1.2	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 10mA$		100		MHz
C _{ob}	Output Capacitance	V _{CB} = 50V, f = 1MHz		3	4.5	pF

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Typical Characteristics

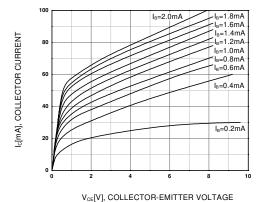


Figure 1. Static Characteristic

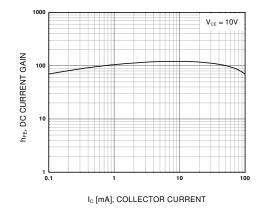


Figure 2. DC current Gain

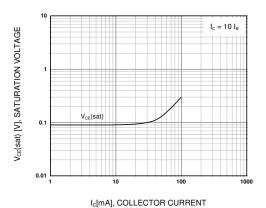


Figure 3. Collector-Emitter Saturation Voltage

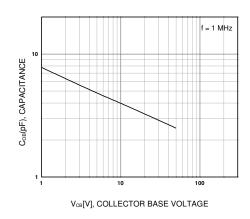


Figure 4. Collector Output Capacitance

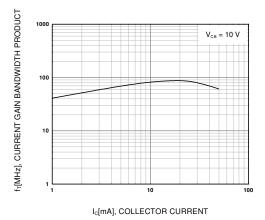


Figure 5. Current Gain Bandwidth Product

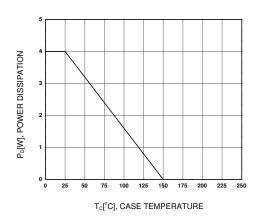
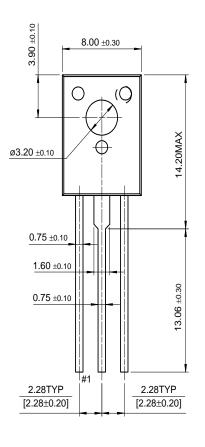
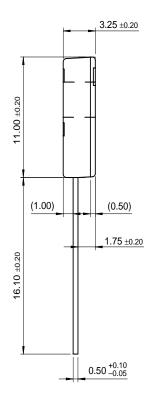


Figure 6. Power Derating

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Dimensions in Millimeters

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